

2SD2620J

Silicon NPN epitaxial planer type

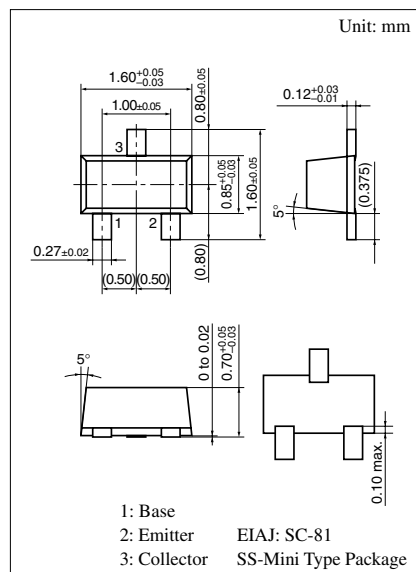
For low-frequency amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- High emitter to base voltage V_{EBO}
- SS-mini type package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	100	V
Emitter to base voltage	V_{EBO}	15	V
Peak collector current	I_{CP}	50	mA
Collector current	I_C	20	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



Marking Symbol: 3B

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 60\text{ V}, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 60\text{ V}, I_B = 0$			1.0	μA
Collector to base voltage	V_{CBO}	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	100			V
Collector to emitter voltage	V_{CEO}	$I_C = 1\text{ mA}, I_B = 0$	100			V
Emitter to base voltage	V_{EBO}	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	15			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 10\text{ V}, I_C = 2\text{ mA}$	400		1 200	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$		0.05	0.2	V
Transition frequency	f_T	$V_{CB} = 10\text{ V}, I_E = -2\text{ mA}, f = 200\text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}, GB = 80\text{ dB}$ $R_g = 100\text{ k}\Omega$, Function = FLAT		80		mV